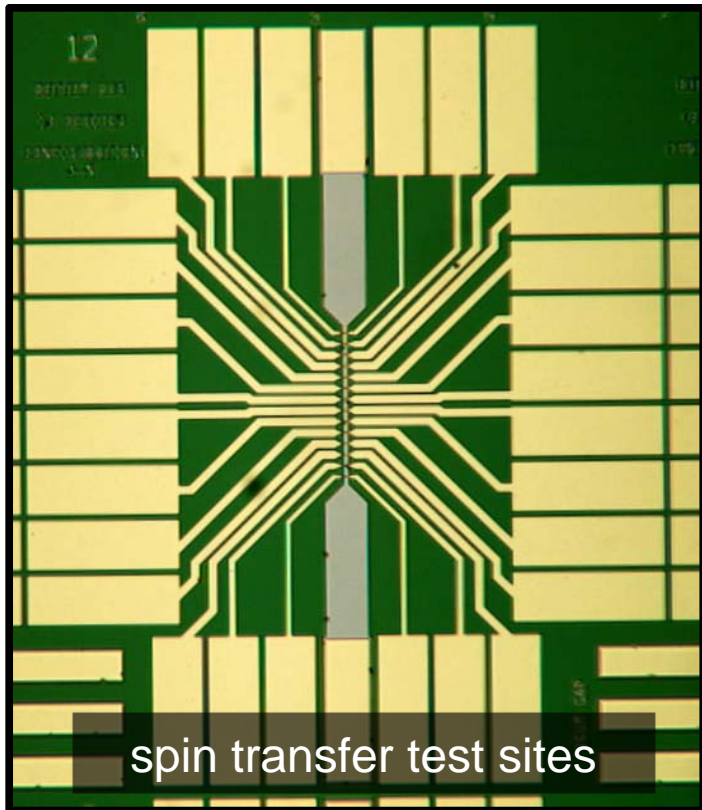


Spin Transfer Devices

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Michael Rogosky, *Spin Transfer Technologies, LLC* (<http://www.spintransfer.com/>).



The Penn State NNIN site is being used to fabricate prototype magneto-resistive random access memory (MRAM) devices that are of interest for non-volatile computer memory.

The MRAM devices use a quantum mechanical effect known as spin transfer to manipulate magnetic orientations. This provides higher write speeds, lower power consumption, and scalability to next generation non-volatile memory process technologies.

Advantages of spin transfer magnetic random access memory devices include faster switching times and scalability to smaller dimensions.

Penn State Site

